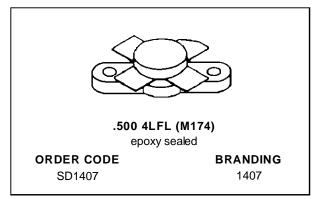
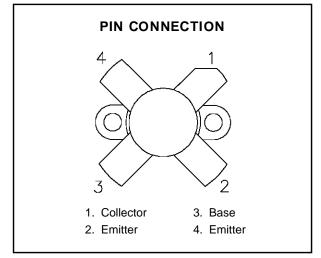


SD1407

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

- 30 MHz
- 28 VOLTS
- IMD -30 dB
- COMMON EMITTER
- GOLD METALLIZATION
- Pout = 125 W MIN. WITH 15 dB GAIN





DESCRIPTION

The SD1407 is a 28 V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes state-of-the-art diffused emitter ballasting for improved ruggedness and reliability.

ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CEO}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	20	А
P _{DISS}	P _{DISS} Power Dissipation		W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance	0.65	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions	Value			Unit		
	rest conditions		Min.	Тур.	Max.	OIIII	
ВУсво	I _C = 100mA	$I_E = 0mA$		65	_	_	V
BVces	I _C = 100mA	$V_{BE} = 0V$		65	_		V
BV _{CEO}	I _C = 100mA	$I_B = 0mA$		35	_	_	V
BV _{EBO}	I _E = 10mA	$I_C = 0mA$		4.0	_		V
Ices	V _{CE} = 30V	I _E = 0mA		_	_	15	mA
hFE	V _{CE} = 5V	Ic = 5A		10	_	200	_

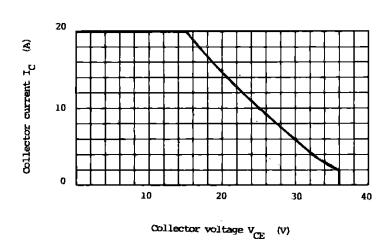
DYNAMIC

Symbol	Test Conditions			Value			Unit
Symbol				Min.	Тур.	Max.	Oiiit
Pout	f = 30 MHz	$P_{IN} = 3.95 \text{ W}$	$V_{CE} = 28 V$	125	_	_	W
G _P	f = 30 MHz	$P_{IN} = 3.95 \text{ W}$	$V_{CE} = 28 \text{ V}$	15	16	_	dB
IMD*	f = 30 MHz	V _{CE} = 28 V	$I_{CQ} = 100 \text{ mA}$	_	-34	-30	dB
Сов	f = 1 MHz	$V_{CB} = 30 V$		_	250	_	pF

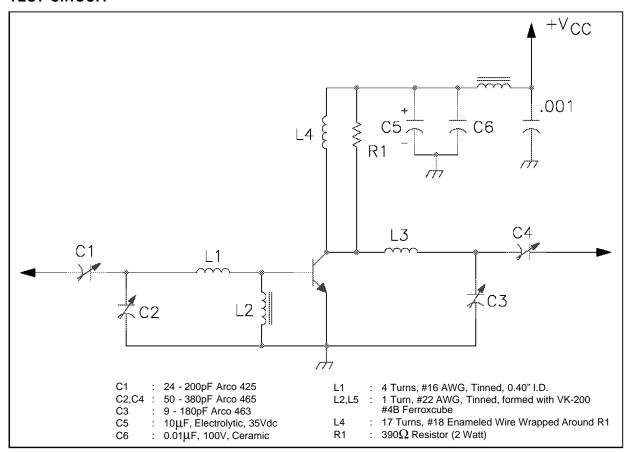
Note: $^*P_{OUT} = 100W PEP$, $f_O = 30 + 30.001 MHz$

TYPICAL PERFORMANCE

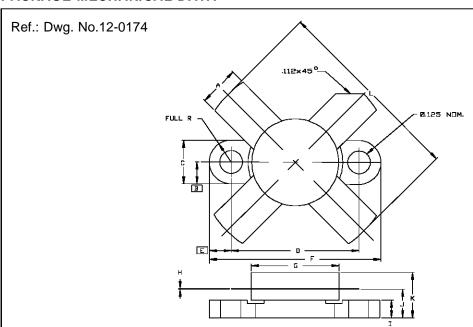
SAFE OPERATING AREA



TEST CIRCUIT



PACKAGE MECHANICAL DATA



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAX[MUM Inches/mm		MINIMUM Inches/mm	MAX[MUM Inches/mm
Α	.220/5,59	.230/5,84	K		.280/7,11
В	.125/3,18		L		1.050/26,67
С	.245/6,22	.255/6,48			
D	.720/18,28	.730/18,54			
Ε	.125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
Н	.003/0,08	.007/0,18			
I	.090/2,29	110/2,79			
J	.160/4,06	.175/4,45			

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